



# JSKT095/JSKH095

## Description

- 1) A package of series of two chips.
- 2) With high thermal conductivity DBC as the insulation.
- 3) Welding by vacuum welding technology, which provide high reliability.



## Typical Application

DC motor control, temperature control and light control system.

## Absolute Maximum Ratings (Packaged into modules, unless otherwise specified, T<sub>CASE</sub>=25 )

| Parameter                            | Test Conditions | Symbol         | Values |      |      | Unit |
|--------------------------------------|-----------------|----------------|--------|------|------|------|
|                                      |                 |                | 12     | 16   | 18   |      |
| Operating junction temperature range |                 | T <sub>J</sub> | -25    | 1200 | 1600 | 1800 |

|   |  |  |           |      |      |                  |
|---|--|--|-----------|------|------|------------------|
| Non-repetitive peak off-state voltage     | T <sub>J</sub> =25                                       | V <sub>DSM</sub>                       | 1300      | 1700 | 1900 | V                |
| Non-repetitive peak reverse voltage       | T <sub>J</sub> =25                                       | V <sub>RSM</sub>                       | 1300      | 1700 | 1900 | V                |
| Average on-state current                  | T <sub>C</sub> =85                                       | I <sub>T(AV)</sub> /I <sub>F(AV)</sub> | 90        |      |      | A                |
| Peak on-state surge current               | t <sub>P</sub> =10ms V <sub>R</sub> =0.6V <sub>RSM</sub> | I <sub>TSM</sub> /I <sub>FSM</sub>     | 1800      |      |      | A                |
| I <sup>2</sup> t value for fusing         | t <sub>P</sub> =10ms V <sub>R</sub> =0.6V <sub>RSM</sub> | I <sup>2</sup> t                       | 16200     |      |      | A <sup>2</sup> s |
| Critical rate of rise of on-state current | I <sub>G</sub> =2×I <sub>GT</sub>                        | di/dt                                  | 150       |      |      | A/μs             |
| Insulation voltage                        | A.C 50Hz(1s/1min)  | V <sub>ISO</sub>                       | 3600/3000 |      |      | V                |

## Electrical Characteristics (Packaged into modules, unless otherwise specified, T<sub>CASE</sub>=25 )

| Parameter                         | Test Conditions  | Symbol            | Values | Unit |
|-----------------------------------|--|-------------------|--------|------|
| Peak on-state voltage             | I <sub>T</sub> =270A t <sub>P</sub> =380μs             | V <sub>TM</sub>   | 1.8    | V    |
| Threshold voltage                 | T <sub>J</sub> =125                                    | V <sub>TO</sub>   | 0.95   | V    |
| Dynamic resistance                | T <sub>J</sub> =125                                    | R <sub>d</sub>    | 2.1    | m    |
| Repetitive peak off-state current | V <sub>D</sub> =V <sub>DRM</sub><br>T <sub>C</sub> =25 | I <sub>DRM1</sub> | 100    | μA   |
|                                   | T <sub>C</sub> =125                                    | I <sub>DRM2</sub> | 30     | mA   |

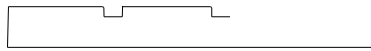


|                                  |  |                                |              |               |
|----------------------------------|--|--------------------------------|--------------|---------------|
| Repetitive peak reverse current  | $V_R = V_{RRM}$<br>$T_C = 25$<br>$T_C = 125$ | $I_{RRM1}$<br>$I_{RRM2}$       | 100<br>30    | $\mu A$<br>mA |
| Triggering gate current          | $V_D = 12V$ $R_L = 30$                       | $I_{GT}$                       | 20-120       | mA            |
| Holding current                  | $I_T = 1A$                                   | $I_H$                          | 250          | mA            |
| Latching current                 | $I_G = 1.2 I_{GT}$                           | $I_L$                          | 300          | mA            |
| Triggering gate voltage          | $V_D = 12V$ $R_L = 30$                       | $V_{GT}$                       | 1.8          | V             |
| Non triggering gate voltage      | $V_D = V_{DRM}$ $T_J = 125$                  | $V_{GD}$                       | 0.25         | V             |
| Critical rate of rise of voltage | $V_D = 2/3 V_{DRM}$ $T_J = 125$<br>Gate Open | $dv/dt$                        | 1000         | V/ $\mu s$    |
| Thermal resistance               | Junction to case<br>Case to heatsink         | $R_{th(j-c)}$<br>$R_{th(c-s)}$ | 0.30<br>0.22 | $\wedge W$    |



### Mechanical Characteristics

|                                      |           |
|--------------------------------------|-----------|
| Module size                          | 93mm×21mm |
| Module height                        | 30mm      |
| Terminal distance of (1) / (2) / (3) | 20mm      |
| Mounting torque(M5)                  | 5±15%Nm   |
| Terminal torque(M5)                  | 3±15%Nm   |



0 0 0 0 0 0 0 0

0 0 0 0 0 0 0 0

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FIG.3:

